

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO
FIS920010293US2

SERIAL NO.
10/706,773

Edward Barth et al.

FILING 11/12/03

GROUP
2811

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
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| V | 5,679,169 | 10/21/1997 | Gonzales et al. | - | - | - |
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| DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION | |
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| V | 2000 IEEE, A High performamnce 0.13um Copper BEOL Technology with Low-k Dielectric, R.D. Goldblatt et al., IBM Semiconductor Research and Development Center, Hopewell Junction, NY, Infineon Technologies Inc. |

EXAMINER

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DATE CONSIDERED

10/12/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

FIS920010293US 2

Application Number

10/706,773

Applicant(s)

Edward Barth, et al.

Filing Date

November 12, 2003

Group Art Unit

2811
Not Yet Assigned

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
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| ✓ | | 6,071,809 | 06/2000 | Zhao, Bin | — | — | — |
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FOREIGN PATENT DOCUMENTS

| | REF | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | Translation | |
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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